



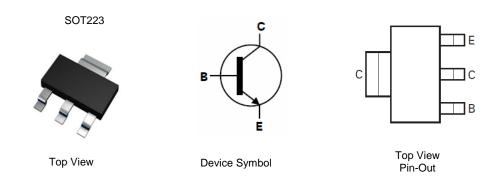
#### **10V NPN MEDIUM POWER TRANSISTOR IN SOT223**

#### **Features**

- BV<sub>CEO</sub> > 10V
- I<sub>C</sub> = 5A High Continuous Collector Current
- I<sub>CM</sub> = 20A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> <45mV @ 500mA</li>
- R<sub>SAT</sub> = 44mΩ @ 5A for a Low Equivalent On-Resistance
- h<sub>FE</sub> Specified up to 20A for a High Gain Hold-Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

### **Mechanical Data**

- Package: SOT223
- Package Material: Molded Plastic. "Green" Molding Compound;
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.112 grams (Approximate)



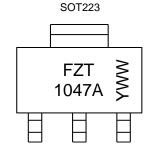
#### Ordering Information (Note 4)

| Orderable Part Number | Marking  | Pool size (inches) | Tape width (mm)  | Packing  |         |  |
|-----------------------|----------|--------------------|------------------|----------|---------|--|
| Orderable Part Number | Warking  | Reel size (inches) | rape width (min) | Quantity | Carrier |  |
| FZT1047ATA            | FZT1047A | 7                  | 12               | 1,000    | Reel    |  |

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

#### **Marking Information**



FZT 1047A = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5 = 2015) WW or  $\overline{W}W$  = Week Code (01~53)



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

| Characteristic               | Symbol         | Value | Unit |
|------------------------------|----------------|-------|------|
| Collector-Base Voltage       | $V_{CBO}$      | 35    | V    |
| Collector-Emitter Voltage    | $V_{\sf CEO}$  | 10    | V    |
| Emitter-Base Voltage         | $V_{EBO}$      | 7     | V    |
| Continuous Collector Current | Ic             | 5     | Α    |
| Peak Pulse Current           | Ісм            | 20    | Α    |
| Base Current                 | I <sub>B</sub> | 500   | mA   |

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                          | Symbol   | Value                             | Unit        |      |  |
|---|----------|-----------------------------------|-------------|------|--|
|   | (Note 5) |                                   | 3           |      |  |
| Bower Dissination                       | (Note 6) | <b>D</b>                          | 2           | W    |  |
| Power Dissipation                       | (Note 7) | $P_D$                             | 1.6         |      |  |
|   | (Note 8) |                                   | 1.2         |      |  |
|   | (Note 5) |                                   | 41.7        |      |  |
| Thermal Desistance, Junction to Ambient | (Note 6) |                                   | 62.5        | °C/W |  |
| Thermal Resistance, Junction to Ambient | (Note 7) | $R_{	heta JA}$                    | 78.1        |      |  |
|   | (Note 8) |                                   | 104         | 1    |  |
| Thermal Resistance Junction to Lead     | (Note 9) | $R_{	hetaJL}$                     | 10.9        |      |  |
| Operating and Storage Temperature Range |          | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |  |

### ESD Ratings (Note 10)

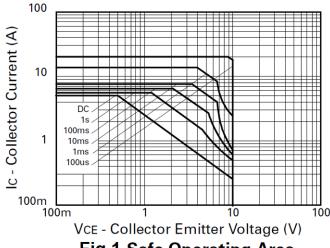
| Characteristic                             | Symbol  | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V    | 3A          |
| Electrostatic Discharge - Machine Model    | ESD MM  | 400   | V    | С           |

Notes:

- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
   6. Same as note (5), except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as note (5), except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating Information**





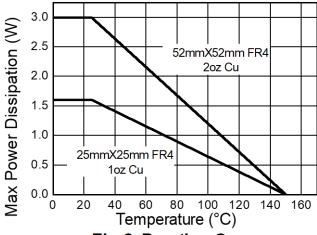


Fig.2 Derating Curve

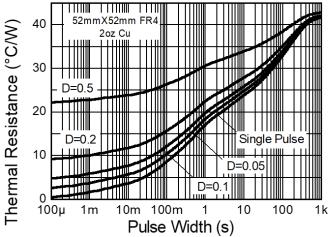


Fig.3 Transient Thermal Impedance

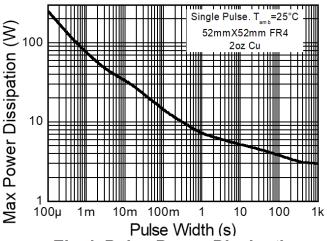


Fig.4 Pulse Power Dissipation



## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                 | Symbol               | Min | Тур | Max  | Unit | Test Condition                                |
|--|----------------------|-----|-----|------|------|---|
| Collector-Base Breakdown Voltage               | BV <sub>CBO</sub>    | 35  | 65  | _    | V    | I <sub>C</sub> = 100μA                        |
| Collector-Emitter Breakdown Voltage            | BV <sub>CES</sub>    | 35  | 55  | _    | V    | I <sub>C</sub> = 100μA                        |
| Collector-Emitter Breakdown Voltage            | BV <sub>CEV</sub>    | 35  | 60  | _    | V    | I <sub>C</sub> = 100μA, V <sub>EB</sub> = 1V  |
| Collector-Emitter Breakdown Voltage (Note 11)  | BV <sub>CEO</sub>    | 10  | 16  | _    | V    | I <sub>C</sub> = 10mA                         |
| Emitter-Base Breakdown Voltage                 | BV <sub>EBO</sub>    | 7   | 8.7 | _    | V    | I <sub>E</sub> = 100μA                        |
| Collector Cut-Off Current                      | I <sub>CBO</sub>     | _   | 0.3 | 10   | nA   | V <sub>CB</sub> = 20V                         |
| Collector Cut-Off Current                      | I <sub>CES</sub>     | _   | 0.3 | 10   | nA   | V <sub>CB</sub> = 20V                         |
| Emitter Cut-Off Current                        | I <sub>EBO</sub>     | _   | 0.3 | 10   | nA   | V <sub>EB</sub> = 4V                          |
|  |                      | _   | 25  | 40   | mV   | I <sub>C</sub> = 500mA, I <sub>B</sub> = 10mA |
| Collector-Emitter Saturation Voltage (Note 11) |                      | _   | 50  | 70   |      | I <sub>C</sub> = 1A, I <sub>B</sub> = 10mA    |
| Collector-Emilier Saturation Voltage (Note 11) | V <sub>CE(sat)</sub> | _   | 140 | 200  |      | I <sub>C</sub> = 3A, I <sub>B</sub> = 15mA    |
|  |                      | _   | 220 | 350  |      | I <sub>C</sub> = 5A, I <sub>B</sub> = 25mA    |
| Base-Emitter Saturation Voltage (Note 11)      | V <sub>BE(sat)</sub> | _   | 925 | 1000 | mV   | I <sub>C</sub> = 5A, I <sub>B</sub> = 25mA    |
| Base-Emitter Turn-On Voltage (Note 11)         | V <sub>BE(on)</sub>  | _   | 890 | 975  | mV   | I <sub>C</sub> = 5A, V <sub>CE</sub> = 2V     |
|  | h <sub>FE</sub>      | 280 | 430 |      |      | $I_C = 10mA$ , $V_{CE} = 2V$                  |
|  |                      | 290 | 440 |      |      | $I_C = 0.5A$ , $V_{CE} = 2V$                  |
| DC Current Gain (Note 11)                      |                      | 300 | 450 | 1200 | _    | $I_C = 1A$ , $V_{CE} = 2V$                    |
|  |                      | 200 | 330 |      |      | $I_C = 5A$ , $V_{CE} = 2V$                    |
|  |                      | 60  | 110 |      |      | $I_C = 20A, V_{CE} = 2V$                      |
| Output Capacitance                             | C <sub>obo</sub>     | _   | 85  | 110  | pF   | V <sub>CB</sub> = 10V, f = 1MHz               |
| Current Gain-Bandwidth Product                 | f⊤                   | _   | 150 | _    | MHz  | $V_{CE} = 10V, I_{C} = 50mA,$<br>f = 50MHz    |
| Switching Times                                | t <sub>on</sub>      |     | 130 | _    |      | I <sub>C</sub> = 4A, V <sub>CC</sub> = 10V,   |
| Switching Times                                | t <sub>off</sub>     | _   | 230 | _    | ns   | $I_{B1} = -I_{B2} = 40 \text{mA}$             |

Note:

11. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2.



# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

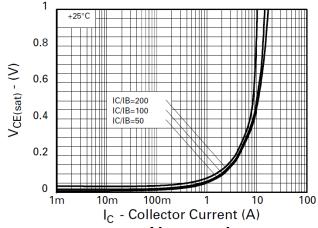


Fig.5 V<sub>CE(sat)</sub> v I<sub>C</sub>

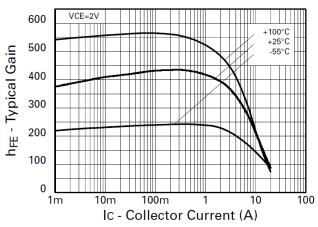


Fig.7 h<sub>FE</sub> v l<sub>C</sub>

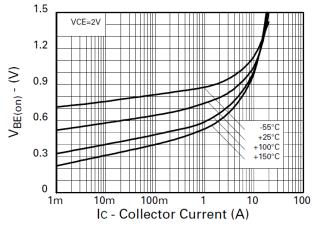


Fig.9 V<sub>BE(on)</sub> v I<sub>C</sub>

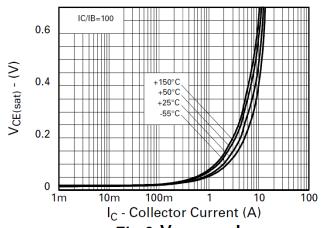


Fig.6 V<sub>CE(sat)</sub> v I<sub>C</sub>

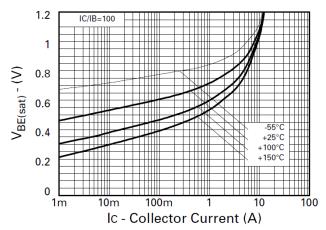


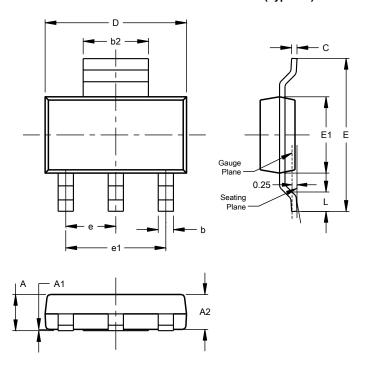
Fig.8 V<sub>BE(sat)</sub> v I<sub>C</sub>



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)

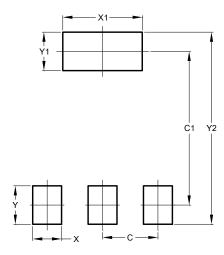


| SOT223 (Type DN)     |      |      |      |  |  |
|----------------------|------|------|------|--|--|
| Dim                  | Min  | Max  | Тур  |  |  |
| Α                    |      | 1.70 |      |  |  |
| A1                   | 0.01 | 0.15 |      |  |  |
| A2                   | 1.50 | 1.68 | 1.60 |  |  |
| b                    | 0.60 | 0.80 | 0.70 |  |  |
| b2                   | 2.90 | 3.10 |      |  |  |
| С                    | 0.20 | 0.32 |      |  |  |
| D                    | 6.30 | 6.70 |      |  |  |
| Е                    | 6.70 | 7.30 |      |  |  |
| E1                   | 3.30 | 3.70 |      |  |  |
| е                    |      |      | 2.30 |  |  |
| e1                   |      |      | 4.60 |  |  |
| L                    | 0.85 |      |      |  |  |
| All Dimensions in mm |      |      |      |  |  |

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)



| Dimensions | Value (in mm) |
|------------|---------------|
| С          | 2.30          |
| C1         | 6.40          |
| Х          | 1.20          |
| X1         | 3.30          |
| Υ          | 1.60          |
| Y1         | 1.60          |
| Y2         | 8.00          |



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